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## Giant dielectric properties with excellent temperature stability of $(\text{Ga}_{0.5}\text{Nb}_{0.5})\text{xTi}_{1-\text{x}}\text{O}_2$ ceramics

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In this work, we investigate the giant dielectric properties of  $(\text{Ga}_{0.5}\text{Nb}_{0.5})\text{xTi}_{1-\text{x}}\text{O}_2$  (where  $x=0.01, 0.025, 0.05$  and  $0.1$ ) prepared by a solid state reaction method. The phase composition, microstructure, and oxidation state are characterized by X-ray diffraction, field-emission scanning electron microscopy and X-ray photoelectron spectroscopy, respectively. The single phase of rutile- $\text{TiO}_2$  with dense microstructure are obtained in all sintered  $(\text{Ga}_{0.5}\text{Nb}_{0.5})\text{xTi}_{1-\text{x}}\text{O}_2$  ceramics. The existence of  $\text{Ti}^{3+}$  and oxygen vacancies are confirmed. The dielectric constant increased with increasing co-doping  $(\text{Ga}+\text{Nb})$  concentration. Excellent dielectric properties are obtained in the  $(\text{Ga}_{0.5}\text{Nb}_{0.5})\text{xTi}_{1-\text{x}}\text{O}_2$  ceramic with  $x=0.1$  sintered at  $1550^\circ\text{C}$  for 1h. Low dielectric loss tangent ( $< 0.05$ ) and very large dielectric constant ( $\epsilon = 41267$ ) with excellent temperature coefficient ( $< \pm 15\%$ ) in the range of  $-70$  to  $170^\circ\text{C}$  are achieved. The giant dielectric response over a broad temperature range of the  $(\text{Ga}_{0.5}\text{Nb}_{0.5})\text{xTi}_{1-\text{x}}\text{O}_2$  ceramics is primarily attributed to the interfacial polarization at internal insulating interfaces.

Keyword:  $\text{TiO}_2$ , Giant dielectric permittivity, Temperature coefficient, Electron-pinned defect-dipole.

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